

IN THE CLAIMS:

C1 1. (Previously Amended) A method of forming wiring in a semiconductor device, comprising the steps of:

forming a polysilicon layer on an insulating film formed on a semiconductor substrate;

forming a metal layer on said polysilicon layer;

depositing a nitride film on said metal layer by a low-pressure chemical vapor deposition method in a single type chamber to form a hard mask layer;

patterning said hard mask layer to form a patterned hard mask;

patterning said metal layer and said polysilicon layer using the patterned hard mask to form a patterned metal layer and said polysilicon layer; and

depositing a nitride film having similar stress characteristics with the hard mask layer by a low-pressure chemical vapor deposition method in the single type chamber and then etching to form a spacer at a sidewall of the patterned metal layer, the patterned polysilicon layer and the patterned hard mask.

2. (Previously Amended) The method of claim 1, wherein the process of depositing the nitride film for forming the hard mask and the spacer is performed in the single type chamber having a temperature of 600°C to 800°C and a pressure of 1 Torr to 500 Torr.

3. (Original) The method of claim 1, wherein said hard mask is formed in a thickness of 500Å to 3000Å.

c) 4. (Original) The method of claim 1, wherein the process of depositing the nitride film for forming the space is performed in a batch type chamber having a temperature of 600°C to 800°C and a pressure of 0.1 Torr to 1 Torr.

5. (Canceled)
